

Product Summary

BV _{DSS}	R _{DS(on)} Max	I _D Max T _A = +25°C
30V	11mΩ @ V _{GS} = 10V	10.5A
	15mΩ @ V _{GS} = 4.5V	9.2A

Features and Benefits

- Low R_{DS(on)} – Ensures On State Losses Are Minimized
- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable And Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMG7430LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
<https://www.diodes.com/quality/product-definitions/>

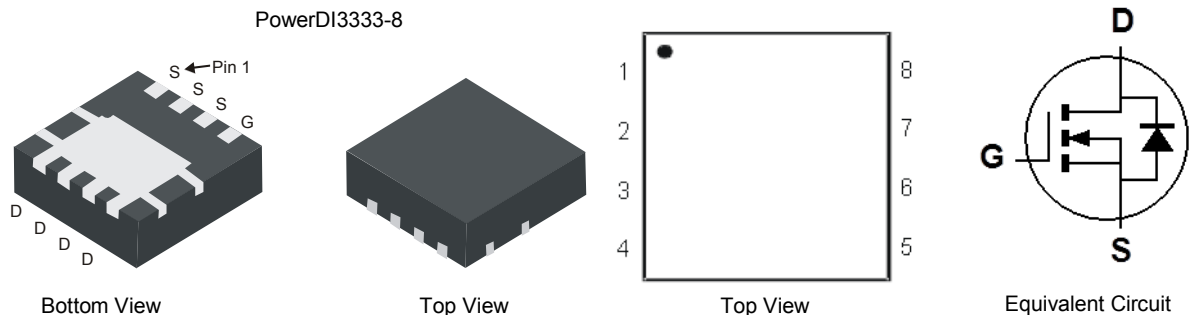
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®] 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)

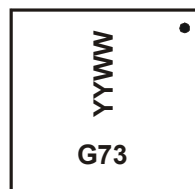


Ordering Information (Note 4)

Part Number	Case	Packaging
DMG7430LFGQ-7	PowerDI3333-8	2000/Tape & Reel
DMG7430LFGQ-13	PowerDI3333-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- G73 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 21 = 2021)
 WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	10.5 8.5	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	14 11	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	90	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3.0	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			I_{AR}	22	A
Repetitive Avalanche Energy (Note 7) $L = 0.1\text{mH}$			E_{AR}	24	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P_D	0.9	W
	$t < 10\text{s}$		1.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	142	$^\circ\text{C/W}$
	$t < 10\text{s}$		78	
Total Power Dissipation (Note 6)	Steady State	P_D	2.2	W
	$t < 10\text{s}$		3.5	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	59	$^\circ\text{C/W}$
	$t < 10\text{s}$		33	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	11	$^\circ\text{C}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

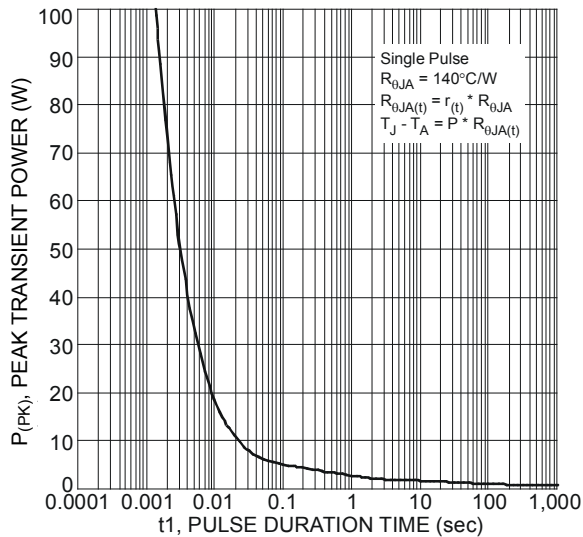


Fig. 1 Single Pulse Maximum Power Dissipation

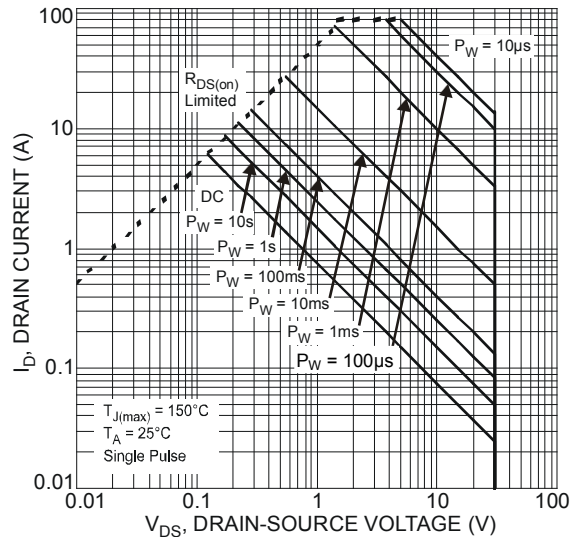
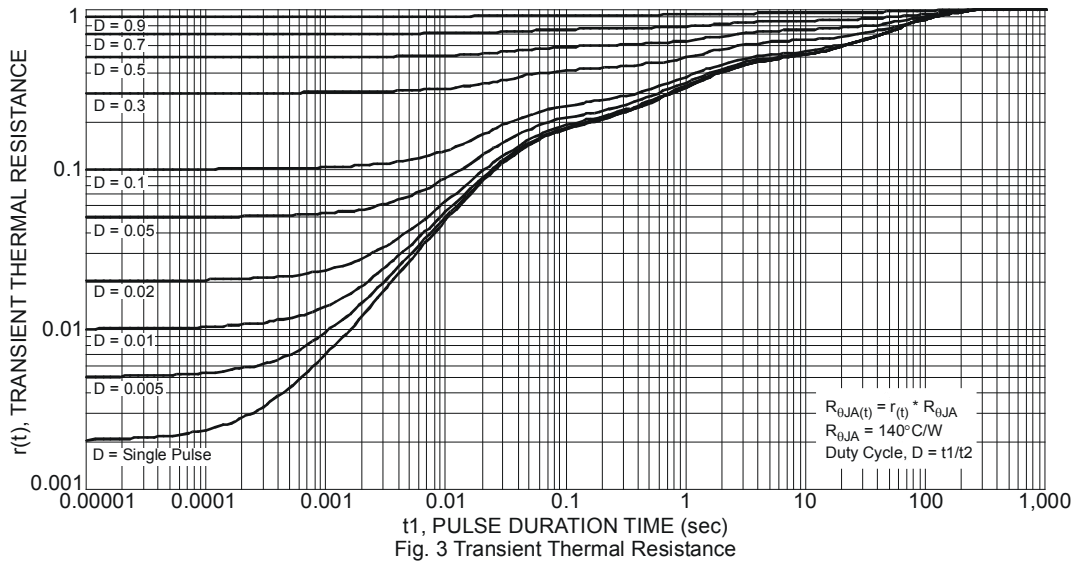


Fig. 2 SOA, Safe Operation Area



Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.4	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	7	11	mΩ	V _{GS} = 10V, I _D = 20A
		—	11	15		V _{GS} = 4.5V, I _D = 20A
Forward Transfer Admittance	Y _{fs}	—	74	—	S	V _{DS} = 5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.75	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1281	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	145	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	125	—	pF	
Gate Resistance	R _g	—	1.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	12.5	—	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	26.7	—	nC	
Gate-Source Charge	Q _{gs}	—	3.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	4.4	—	nC	
Turn-On Delay Time	t _{D(on)}	—	5.2	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω
Turn-On Rise Time	t _R	—	21.2	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	22.3	—	ns	
Turn-Off Fall Time	t _F	—	5.1	—	ns	
Reverse Recovery Time	t _{RR}	—	8.5	—	ns	I _F = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	—	7.0	—	nC	I _F = 12A, di/dt = 500A/μs

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

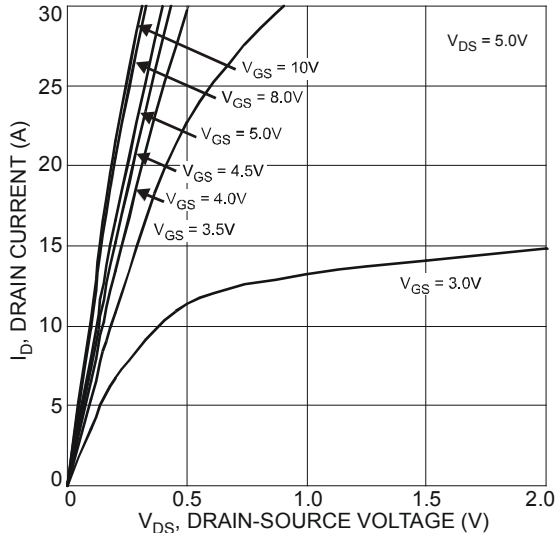


Fig. 4 Typical Output Characteristic

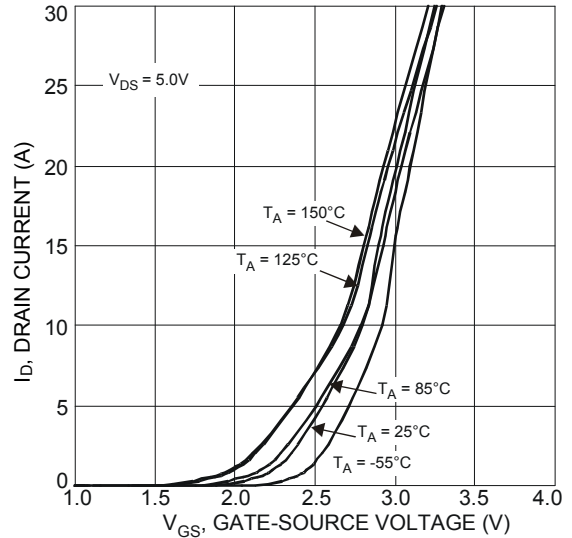


Fig. 5 Typical Transfer Characteristics

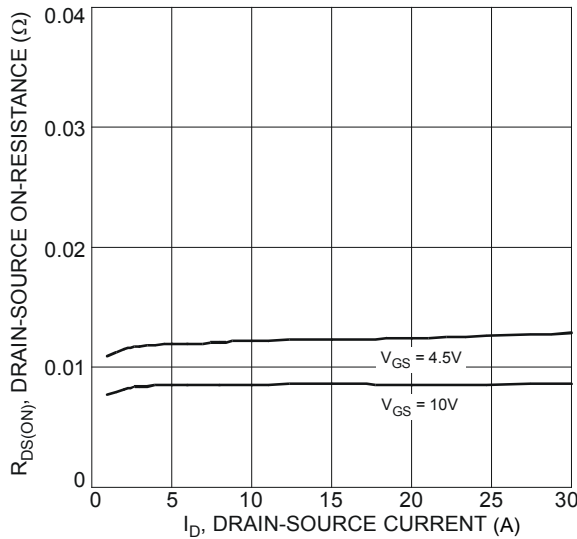


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

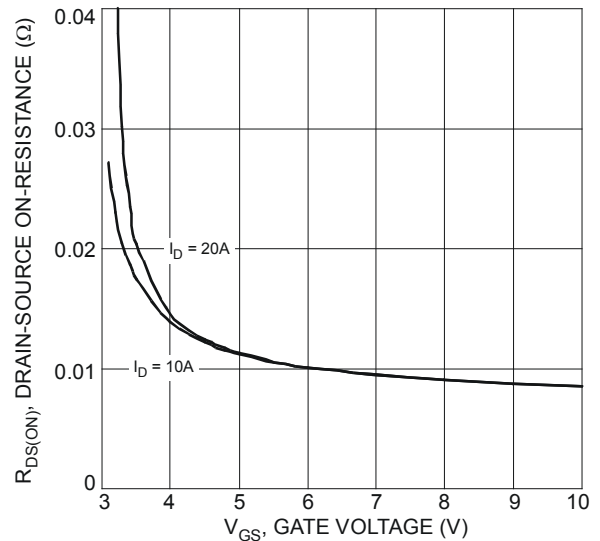


Fig. 7 Typical On-Resistance vs. Gate Voltage

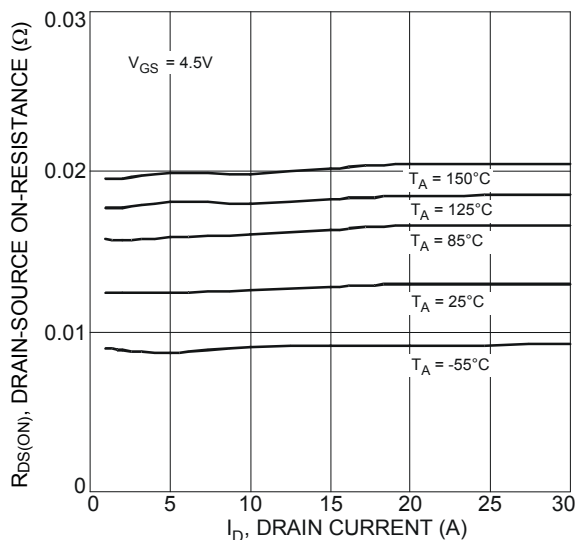


Fig. 8 Typical On-Resistance vs. Drain Current and Temperature

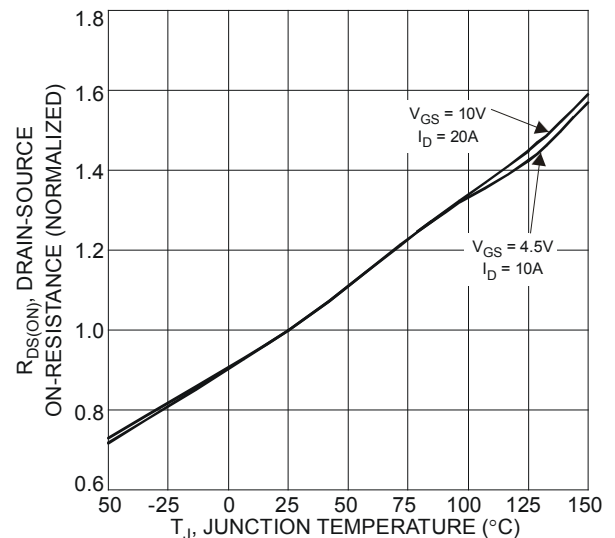


Fig. 9 On-Resistance Variation with Temperature

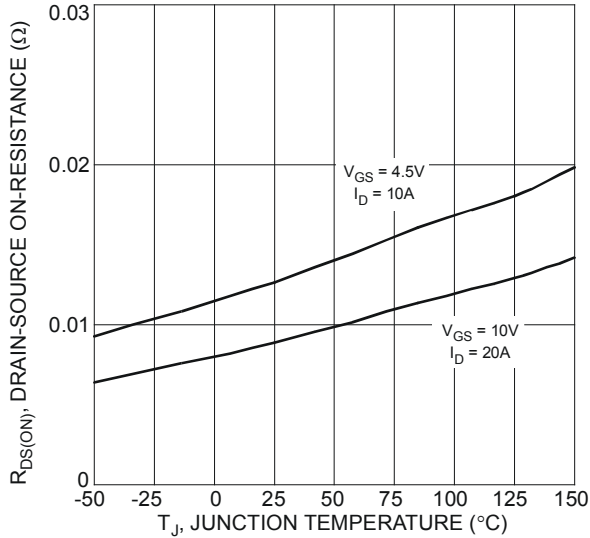


Fig. 10 On-Resistance Variation with Temperature

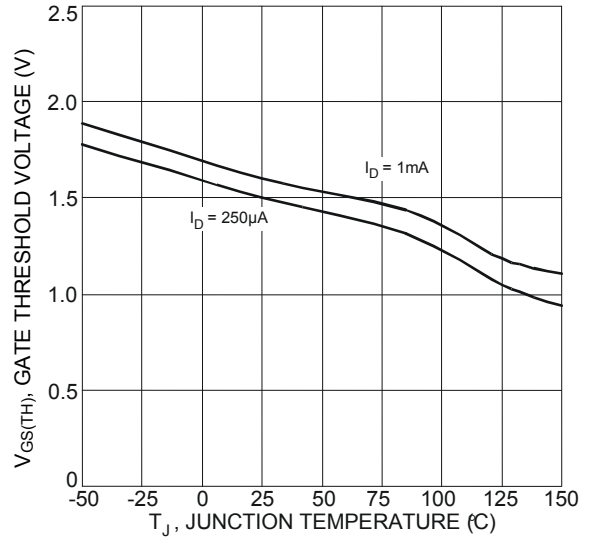


Fig. 11 Gate Threshold Variation vs. Junction Temperature

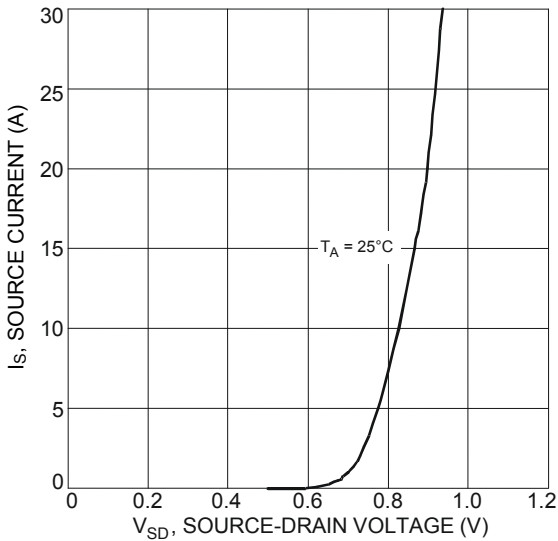


Fig. 12 Diode Forward Voltage vs. Current

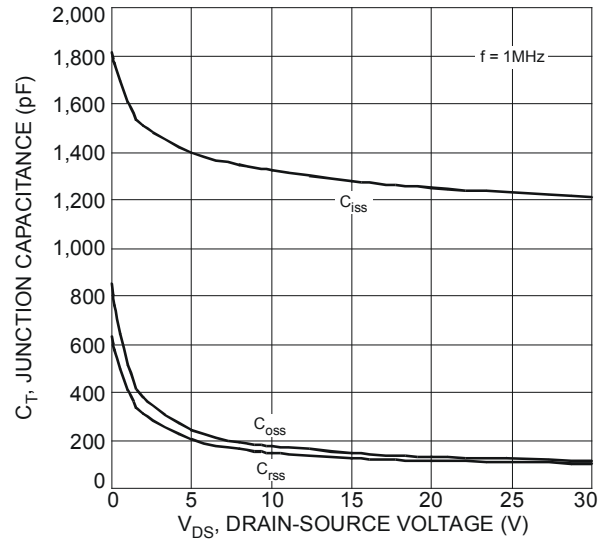


Fig. 13 Typical Junction Capacitance

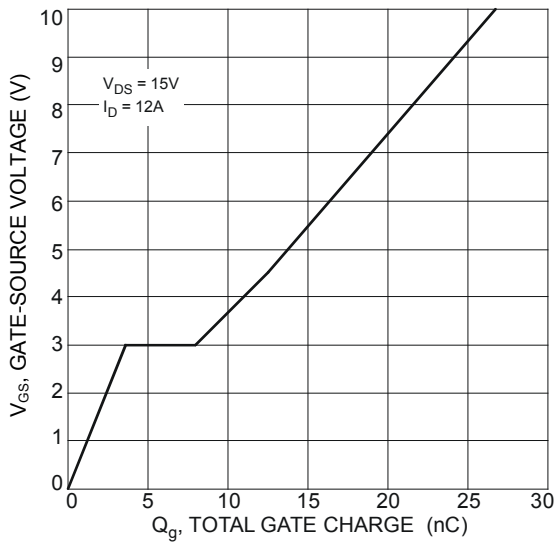
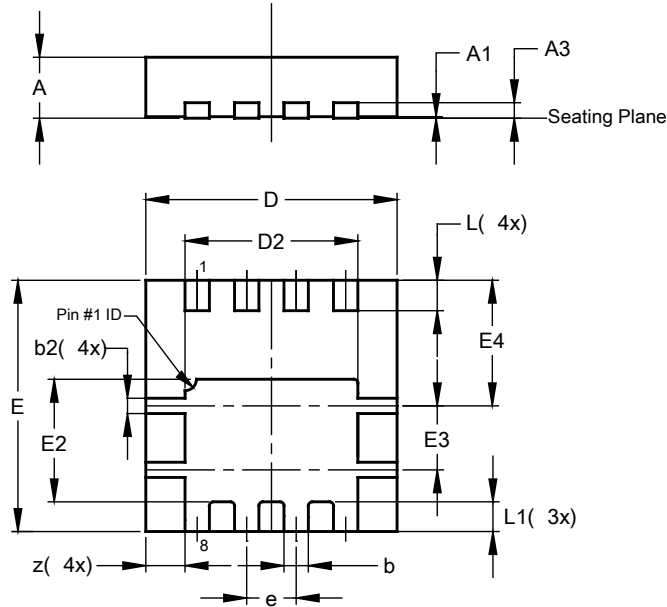


Fig. 14 Gate Charge

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

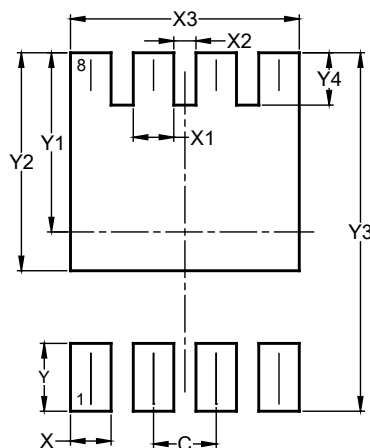


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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